

# **Product Overview**

## NVMFD5C650NL: Dual N-Channel Power MOSFET 60V, 111A, 4.2mΩ

For complete documentation, see the data sheet.

Automotive Power MOSFET in a 5x6mm flat lead package designed for compact and efficient designs and including high thermal performance. Wettable Flank Option available for Enhanced Optical Inspection. AEC-Q101 Qualified MOSFET and PPAP capable suitable for automotive applications.

#### **Features**

- · Small Footprint (5x6 mm) for Compact Design
- Low r<sub>DS(on)</sub> to Minimize Conduction Loss
- Low Q<sub>G</sub> and Capacitance to Minimize Driver Losses
- NVMFD5C650NLWF Wettable Flank Option for Enhanced Optical Inspection
- · AEC-Q101 Qualified and PPAP Capable
- · RoHS Compliant

### **Applications**

- · Solenoid driver
- · Low side / high side driver

## **End Products**

- · Automotive engine controllers
- · Antilock braking systems

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Product	Compliance	Status	Chan nel Polari ty	Confi gurati on	V <sub>(BR)D</sub> SS Min (V)	V <sub>GS</sub> Max (V)	V <sub>GS(th)</sub> Max (V)	I <sub>D</sub> Max (A)	P <sub>D</sub> Max (W)	$\begin{array}{c} R_{DS(on} \\ Max \\ @ \\ V_{GS} = \\ 2.5 \text{ V} \\ (m\Omega) \end{array}$	$\begin{array}{c} R_{DS(on} \\ Max \\ @ \\ V_{GS} = \\ 4.5 \text{ V} \\ (m\Omega) \end{array}$	$R_{DS(on)}$ Max @ $V_{GS} = 10 V$ (m $\Omega$ )	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 4.5 V (nC)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 10 V (nC)	C <sub>iss</sub> Typ (pF)	Pack age Type
NVMFD5C650NLT1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N- Chan nel	Dual	60	±20	2.2	125	125	-	Q1: 5.8, Q2: 5.8	Q1: 4.2, Q2: 4.2	4.7	37	2546	SO- 8FL Dual / DFN- 8
NVMFD5C650NLWFT1G	AEC Qualified PPAP Capable Pb-free Halide free	Active	N- Chan nel	Dual	60	±20	2.2	125	125	-	Q1: 5.8, Q2: 5.8	Q1: 4.2, Q2: 4.2	4.7	37	2546	SO- 8FL Dual / DFN- 8

For more information please contact your local sales support at www.onsemi.com.

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